



SI4465ADY-T1-E3 Information



For Reference Only

Part Number SI4465ADY-T1-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 8V 8SOICPackage8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









SI4465ADY-T1-E3 Specifications

Manufacturer Part Number SI4465ADY-T1-E3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	SI4465ADY-T1-E3
Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Vishay Siliconix
Package8-SOIC (0.154", 3.90mm Width)SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs85nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)3W (Ta), 6.5W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 14A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs85nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)3W (Ta), 6.5W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 14A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature - 55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 8V 8V 8V FET (Metal Oxide) 8V 8V - Vgs (Max) 1.8V, 4.5V 1.8V, 4.5V 1.8V, 4.5V 1.8V, 4.5V 2.85n @ 4.5V 1.8V @ 250μA 85n © 4.5V 1.8V @ 4.5V - Vgs (Max) - Vgs (Max) 3W (Ta), 6.5W (Tc) 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Surface Mount Supplier Device Package 8-SO 8-SOIC (0.154", 3.90mm Width)	Series	TrenchFET?
Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs85nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)3W (Ta), 6.5W (Tc)Rds On (Max) @ Id, Vgs9 mOhm @ 14A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 4.5V°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case - 1.8V, 4.5V - - - - - - - - - - - - -	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	8V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 85nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	-
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	85nC @ 4.5V
FET Feature - Power Dissipation (Max) 3W (Ta), 6.5W (Tc) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9 mOhm @ 14A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs9 mOhm @ 14A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	3W (Ta), 6.5W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	9 mOhm @ 14A, 4.5V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4465ADY-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4465ADY-T1-E3 Payment Methods



















SI4465ADY-T1-E3 Shipping Methods













If you have any question about SI4465ADY-T1-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com